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TITLE: Method for improving water-resistant property of silicon nitride thin film doped with fluorine - by NH3 plasma post-treatment for moisture isolation and sustaining low dielectric constant

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PATENT-FAMILY:

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APPLICATION-DATA:

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ABSTRACTED-PUB-NO: TW 368687A

BASIC-ABSTRACT: A kind of method for improving the water-resistant property of

silicon nitride thin film doped with fluorine which is to apply the NH3 plasma post-treatment on the silicon oxide deposition thin film doped with fluorine under the circumstances enough for the nitrogenizing on the surface of thin film but generally sustaining the original structure so as to isolate the moisture and let the thin film sustain low dielectric constant for a long time.

TITLE-TERMS:

METHOD IMPROVE WATER RESISTANCE PROPERTIES SILICON NITRIDE
THIN FILM DOPE
FLUORINE PLASMA POST TREAT MOIST ISOLATE SUSTAINED LOW
DIELECTRIC CONSTANT

DERWENT-CLASS: L03 U11

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